

2SJ276

# **Ultrahigh-Speed Switching Applications**

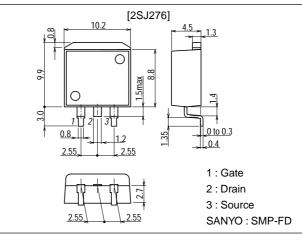
### Features

- $\cdot$  Low ON resistance.
- · Ultrahigh-speed switching.
- · Low-voltage drive.
- Surface mount type device making the following possible.
- Reduction in the assembling time for 2SJ276applied equipment.
- · High-density surface mount applications.
- · Small size of 2SJ276-applied equipment.

### **Package Dimensions**

### unit:mm





## **Specifications**

### Absolute Maximum Ratings at Ta = 25°C

| Parameter                   | Symbol           | Conditions             | Ratings     | Unit |
|-----------------------------|------------------|------------------------|-------------|------|
| Drain-to-Source Voltage     | V <sub>DSS</sub> |                        | -100        | V    |
| Gate-to-Source Voltage      | VGSS             |                        | ±20         | V    |
| Drain Current (DC)          | ۱ <sub>D</sub>   |                        | -8          | A    |
| Drain Current (Pulse)       | I <sub>DP</sub>  | PW≤10µs, duty cycle≤1% | -32         | Α    |
| Allowable Power Dissipation | P-               |                        | 1.65        | W    |
|                             | PD               | Tc=25°C                | 60          | W    |
| Channel Temperature         | Tch              |                        | 150         | °C   |
| Storage Temperature         | Tstg             |                        | -55 to +150 | °C   |

### **Electrical Characteristics at Ta = 25°C**

| Parameter                                  | Symbol              | Conditions                                 | Ratings |      |      | Unit |
|--|---------------------|--|---------|------|------|------|
|  |                     |  | min     | typ  | max  | Onit |
| Drain-to-Source Breakdown Voltage          | V(BR)DSS            | I <sub>D</sub> =-1mA, V <sub>GS</sub> =0   | -100    |      |      | V    |
| Gate-to-Source Breakdown Voltage           | V(BR)GSS            | $I_{G}=\pm 100\mu A$ , $V_{DS}=0$          | ±20     |      |      | V    |
| Zero-Gate Voltage Drain Current            | IDSS                | V <sub>DS</sub> =-100V, V <sub>GS</sub> =0 |         |      | -100 | μΑ   |
| Gate-to-Source Leakage Current             | IGSS                | V <sub>GS</sub> =±16V, V <sub>DS</sub> =0  |         |      | ±10  | μΑ   |
| Cutoff Voltage                             | VGS(off)            | $V_{DS}$ =-10V, I <sub>D</sub> =-1mA       | -1.0    |      | -2.0 | V    |
| Forward Transfer Admittance                | yfs                 | V <sub>DS</sub> =-10V, I <sub>D</sub> =-4A | 3.5     | 6.5  |      | S    |
| Static Drain-to-Source ON-State Resistance | R <sub>DS(on)</sub> | I <sub>D</sub> =-4A, V <sub>GS</sub> =-10V |         | 0.22 | 0.3  | Ω    |
|  | R <sub>DS(on)</sub> | ID=-4A, VGS=-4V                            |         | 0.3  | 0.4  | Ω    |

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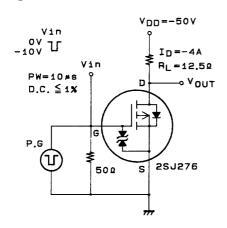
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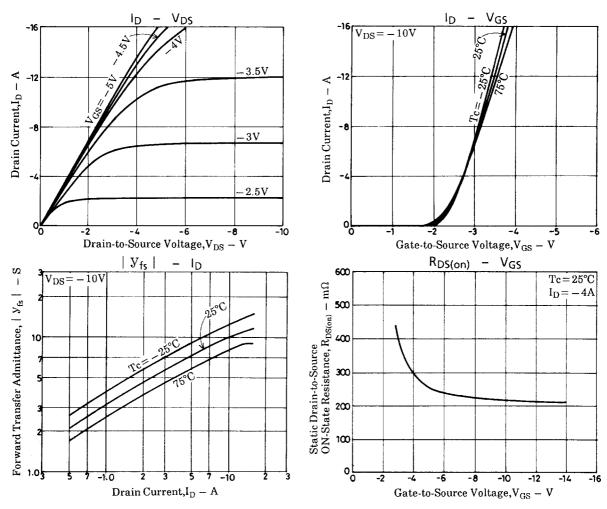
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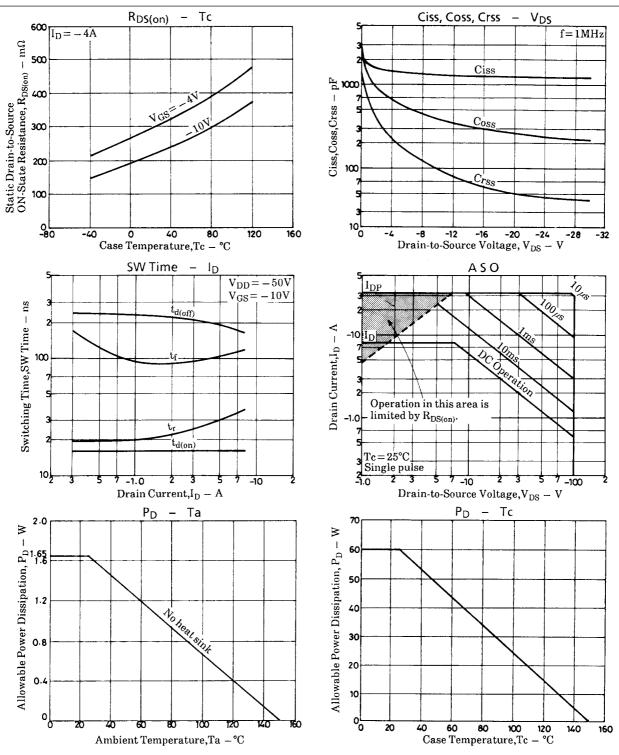
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| Parameter                    | Symbol              | Conditions                              | Ratings |      |      | Unit |
|------------------------------|---------------------|---|---------|------|------|------|
| Falanetei                    |                     |   | min     | typ  | max  | Unit |
| Input Capacitance            | Ciss                | V <sub>DS</sub> =-20V, f=1MHz           |         | 1230 |      | pF   |
| Output Capacitance           | Coss                | V <sub>DS</sub> =-20V, f=1MHz           |         | 260  |      | pF   |
| Reverse Transfer Capacitance | Crss                | V <sub>DS</sub> =-20V, f=1MHz           |         | 50   |      | pF   |
| Turn-ON Delay Time           | <sup>t</sup> d(on)  | See specified Test Circuit              |         | 16   |      | ns   |
| Rise Time                    | tr                  | See specified Test Circuit              |         | 27   |      | ns   |
| Turn-OFF Delay Time          | <sup>t</sup> d(off) | See specified Test Circuit              |         | 200  |      | ns   |
| Fall Time                    | tf                  | See specified Test Circuit              |         | 100  |      | ns   |
| Diode Forward Voltage        | V <sub>SD</sub>     | I <sub>S</sub> =-8A, V <sub>GS</sub> =0 |         | -1.0 | -1.5 | V    |

### **Switching Time Test Circuit**







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